MMVL105GT1

Preferred Device

Silicon Tuning Diode

This device is designed in the Surface Mount package for general frequency control and tuning applications. It provides solid−state reliability in replacement of mechanical tuning methods.

Features

- Controlled and Uniform Tuning Ratio
- Pb−Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	30	Vdc
Peak Forward Current	I_F	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, T_A = 25°C (Note 1) Derate above 25°C	P_D	200 1.57	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	635	°C/W
Junction and Storage Temperature	T_J, T_{stg}	150	°C

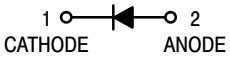
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

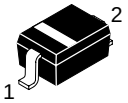
1. FR−4 Minimum Pad

ON Semiconductor®

http://onsemi.com

30 VOLT VOLTAGE VARIABLE CAPACITANCE DIODE





PLASTIC
SOD−323
CASE 477
STYLE 1

MARKING DIAGRAM

4E = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMVL105GT1	SOD−323	3000 / Tape & Reel
MMVL105GT1G	SOD−323 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μAdc)	$V_{(BR)R}$	30	–	–	Vdc
Reverse Voltage Leakage Current (V_R = 28 Vdc)	I_R	–	–	50	nAdc

Device Type	C_T V_R = 25 Vdc, f = 1.0 MHz pF		Q V_R = 3.0 Vdc f = 50 MHz	C_R C_3/C_{25} f = 1.0 MHz	
	Min	Max	Typ	Min	Max
MMVL105GT1	1.5	2.8	250	4.0	6.5

TYPICAL CHARACTERISTICS

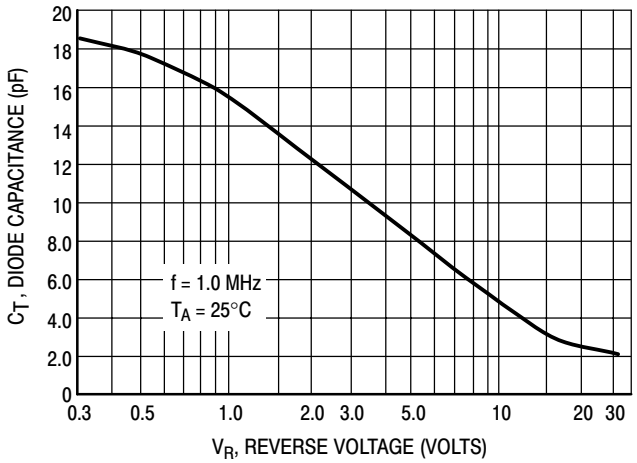


Figure 1. Diode Capacitance

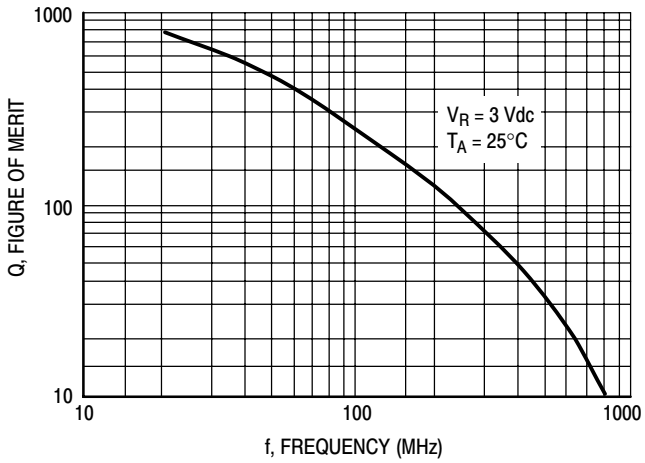


Figure 2. Figure of Merit

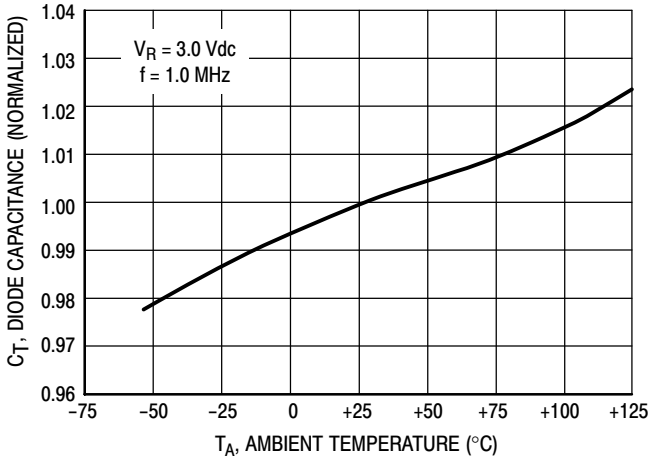
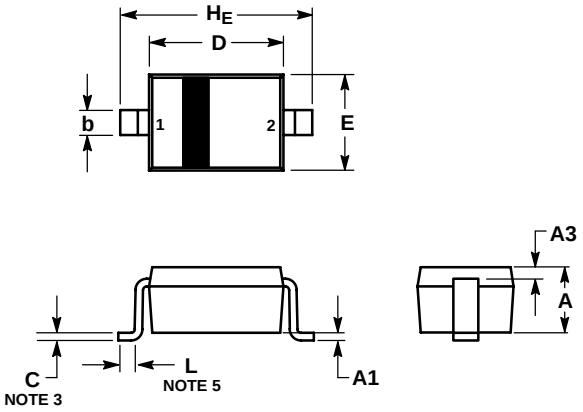


Figure 3. Diode Capacitance

MMVL105GT1

PACKAGE DIMENSIONS

SOD−323
CASE 477−02
ISSUE G

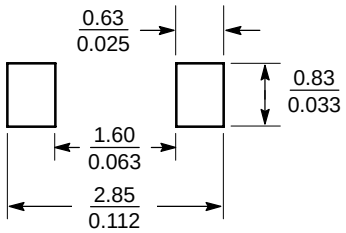


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS			INCHES		
DIM	**MIN**	**NOM**	**MAX**	**MIN**	**NOM**	**MAX**
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
H_E	2.30	2.50	2.70	0.090	0.098	0.105

STYLE 1:
PIN 1. CATHODE
2. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
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2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

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For additional information, please contact your local Sales Representative.

MMVL105GT1/D